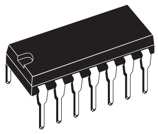
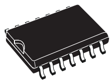
HCF4007UB

DUAL COMPLEMENTARY PAIR PLUS INVERTER

- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- MEDIUM SPEED OPERATION
  t_{PD} = 30ns (Typ.) AT 10V
- QUIESCENT CURRENT SPECIFIED UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT
  I_I = 100nA (MAX) AT V_{DD} = 18V T_A = 25°C
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



DIP



SOP

ORDER CODES

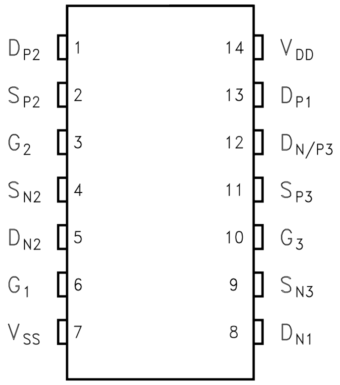
PACKAGE	TUBE	T & R
DIP	HCF4007UBEY	
SOP	HCF4007UBM1	HCF4007UM013TR

DESCRIPTION

The HCF4007UB is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages.

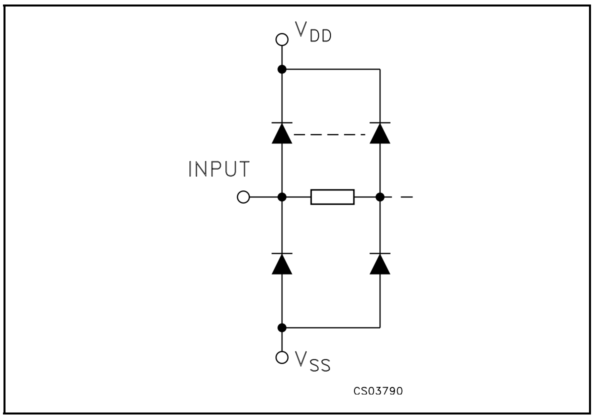
The HCF4007UB type is comprised of three n-channel and three p-channel enhancement type MOS transistors. The transistor elements are accessible through the package terminals to provide a convenient means for constructing the various typical circuits as shown in typical applications. More complex functions are possible using multiple packages. Number shown in parentheses indicate terminals that are connected together to form the various configuration listed.

PIN CONNECTION

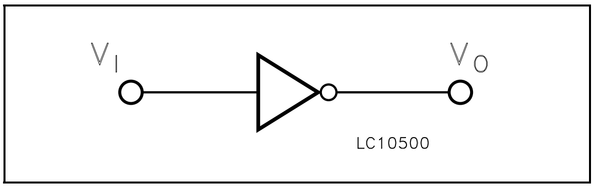


CS05370

INPUT EQUIVALENT CIRCUIT



LOGIC DIAGRAM



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
2, 11	S_{P2}, S_{P3}	Source Connections to 2nd and 3rd p-channel transistors
13, 1	D_{P1}, D_{P2}	Drain Connections from the 1st and 2nd p-channel transistors
8, 5	D_{N1}, D_{N2}	Drain Connections from the 1st and 2nd n-channel transistors
4, 9	S_{N2}, S_{N3}	Source Connections to the 2nd and 3rd n-channel
12	$D_{N/P3}$	Common connection to the 3rd p-channel and n-channel transistor drains
6, 3, 10	G_1 to G_3	Gate connections to n-channel and p-channel of the three transistor pairs
7	V_{SS}	Negative Supply Voltage
14	V_{DD}	Positive Supply Voltage

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	-0.5 to +22	V
V_I	DC Input Voltage	-0.5 to V_{DD} + 0.5	V
I_I	DC Input Current	± 10	mA
P_D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T_{op}	Operating Temperature	-55 to +125	°C
T_{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	3 to 20	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

Symbol	Parameter	Test Condition				Value							Unit
		V_I (V)	V_O (V)	$\lvert I_O \rvert$ (µA)	V_{DD} (V)	T_A = 25°C			-40 to 85°C		-55 to 125°C		
						Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
I_L	Quiescent Current	0/5			5		0.01	0.25		7.5		7.5	µA
		0/10			10		0.01	0.5		15		15	
		0/15			15		0.01	1		30		30	
		0/20			20		0.02	5		150		150	
V_{OH}	High Level Output Voltage	0/5		<1	5	4.95			4.95		4.95		V
		0/10		<1	10	9.95			9.95		9.95		
		0/15		<1	15	14.95			14.95		14.95		
V_{OL}	Low Level Output Voltage	5/0		<1	5		0.05			0.05		0.05	V
		10/0		<1	10		0.05			0.05		0.05	
		15/0		<1	15		0.05			0.05		0.05	
V_{IH}	High Level Input Voltage		0.5/4.5	<1	5	4			4		4		V
			1/9	<1	10	8			8		8		
			1.5/13.5	<1	15	12.5			12.5		12.5		
V_{IL}	Low Level Input Voltage		4.5/0.5	<1	5			1		1		1	V
			9/1	<1	10			2		2		2	
			13.5/1.5	<1	15			2.5		2.5		2.5	
I_{OH}	Output Drive Current	0/5	2.5	<1	5	-1.36	-3.2		-1.15		-1.1		mA
		0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
I_{OL}	Output Sink Current	0/5	0.4	<1	5	0.44	1		0.36		0.36		mA
		0/10	0.5	<1	10	1.1	2.6		0.9		0.9		
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
I_I	Input Leakage Current	0/18	Any Input		18		$\pm 10^{-5}$	±0.1		±1		±1	µA
C_I	Input Capacitance		Any Input				5	7.5					pF

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD}=5V, 2V min. with V_{DD}=10V, 2.5V min. with V_{DD}=15V

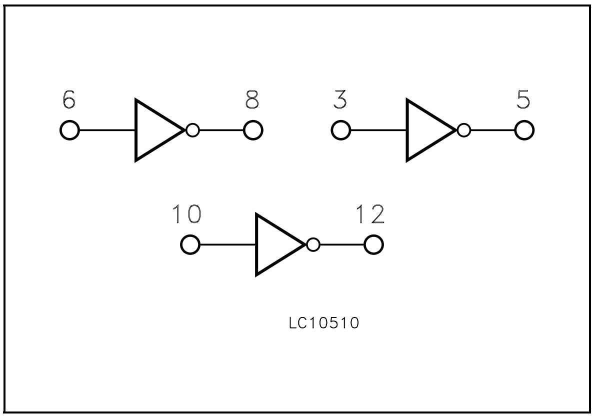
DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200KΩ, $t_r = t_f$ = 20 ns)

Symbol	Parameter	Test Condition		Value (*)			Unit
		V_{DD} (V)		Min.	Typ.	Max.	
t_{PLH} t_{PHL}	Propagation Delay Time	5			55	110	ns
		10			30	60	
		15			25	50	
t_{TLH} t_{THL}	Transition Time	5			100	200	ns
		10			50	100	
		15			40	80	

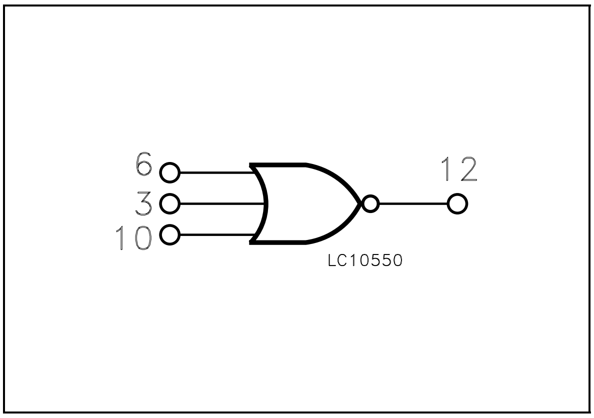
(*) Typical temperature coefficient for all V_{DD} value is 0.3 %/°C.

TYPICAL APPLICATIONS

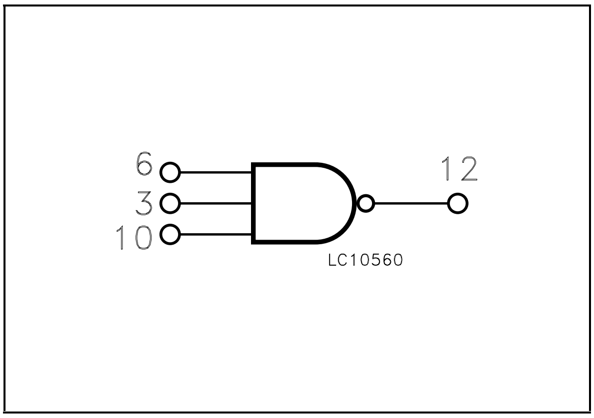
TRIPLE INVERTERS : (14, 2, 11); (8,13); (1, 5); (4, 7, 9)



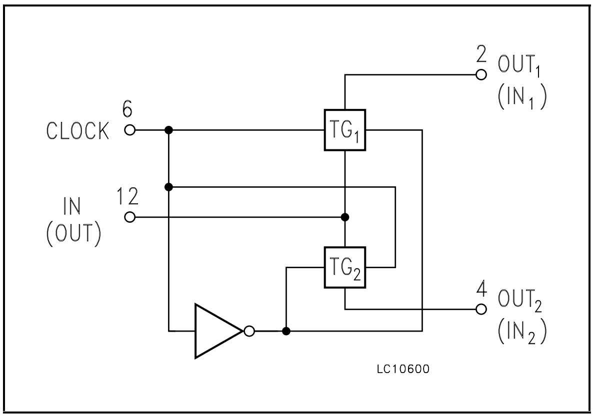
3-INPUT NOR GATE : (13, 2); (1, 11); (12, 5, 8); (4, 7, 9)



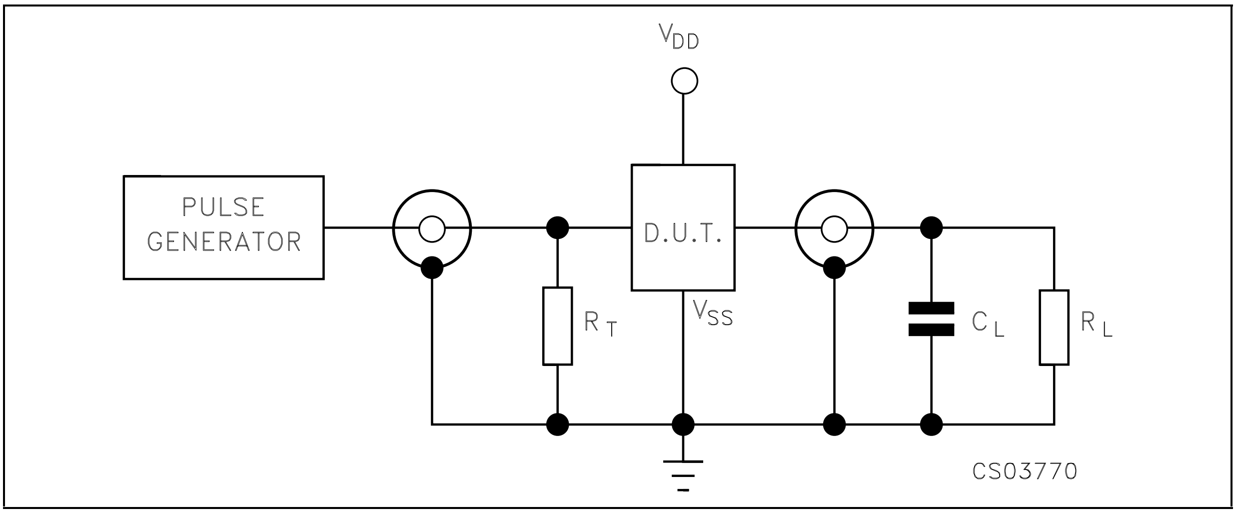
3-INPUT NAND GATE : (1, 12, 13); (2, 14, 11); (4, 8); (5, 9)



DUAL BIDIRECTIONAL TRASMISSION GATING : (1, 5, 12); (2, 9); (11, 4); (8,13,10); (6, 3)

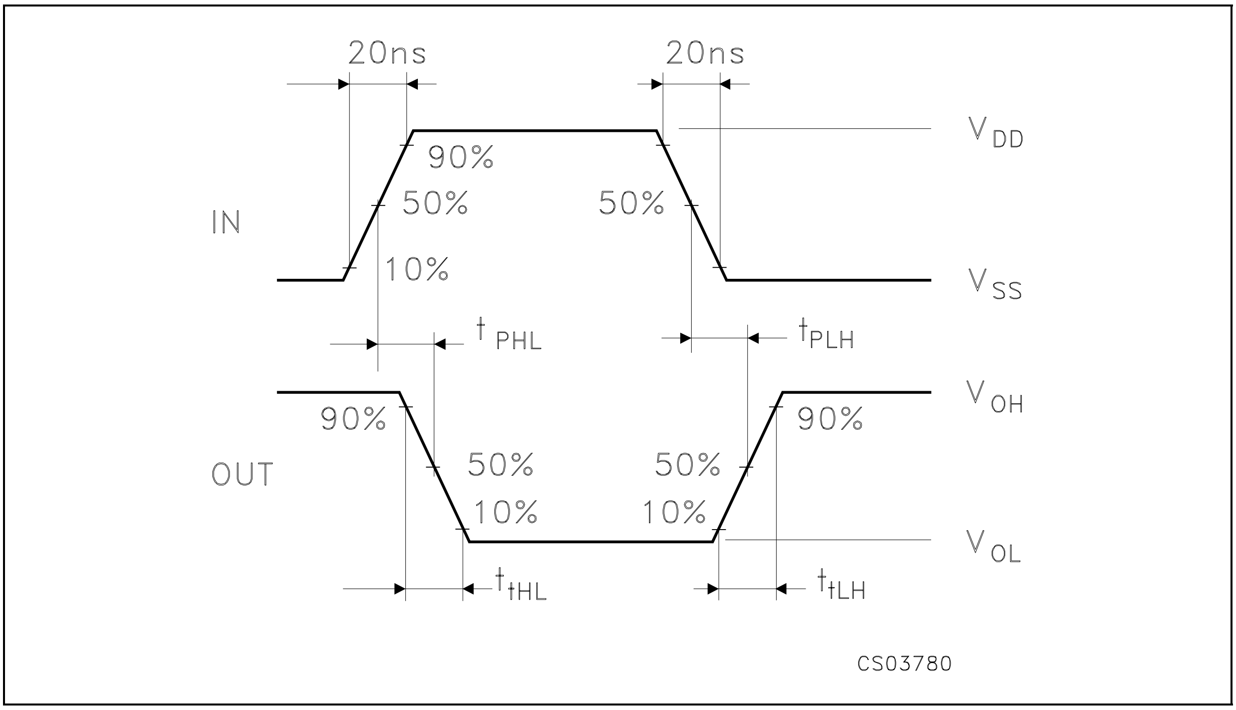


TEST CIRCUIT



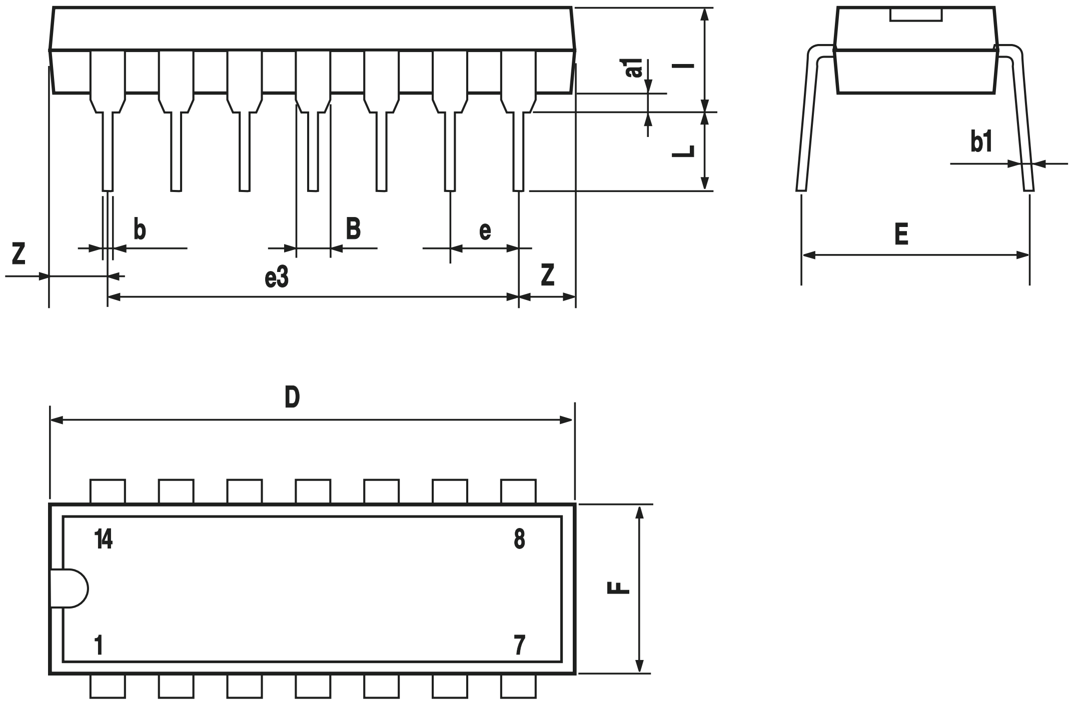
C_L = 50pF or equivalent (includes jig and probe capacitance)
R_L = 200KΩ
R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM : PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



Plastic DIP-14 MECHANICAL DATA

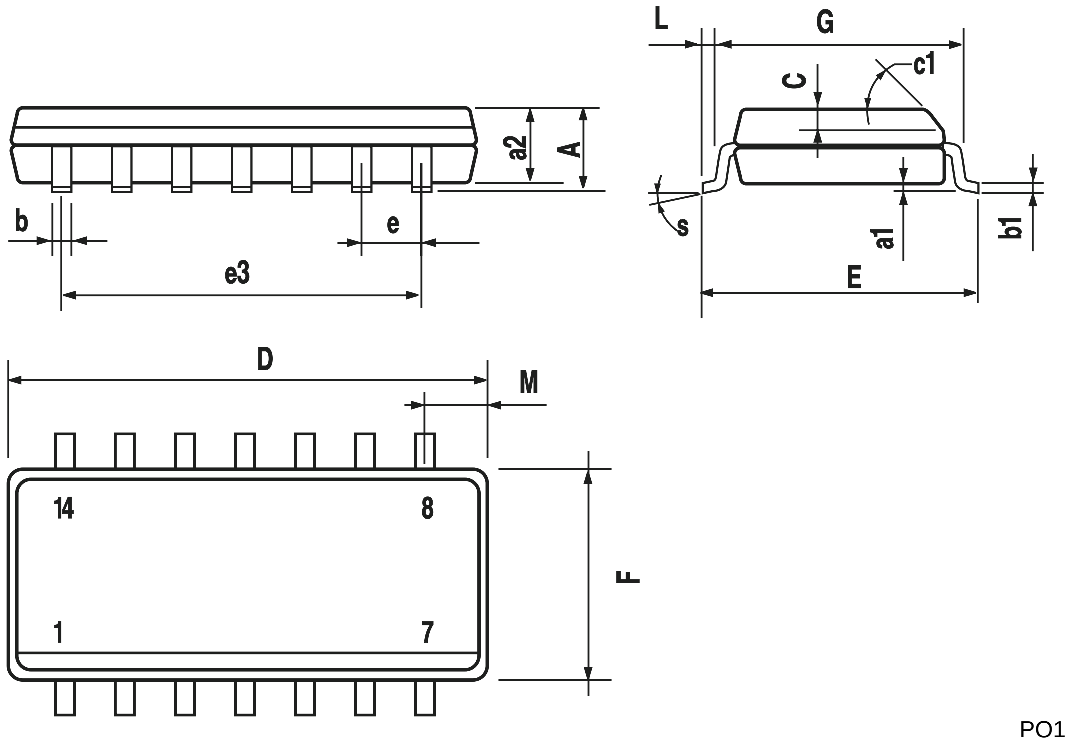
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



P001A

SO-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



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